

BUK9M43-100E

N-channel 100 V, 43 m Ω logic level MOSFET in LFPAK33 2 October 2017

Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- · Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	100	V	
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	25	Α	
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	75	W	
Static chara	acteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	35	43	mΩ	
Dynamic characteristics								
Q_{GD}	gate-drain charge	I _D = 5 A; V _{DS} = 80 V; V _{GS} = 5 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>		-	8.2	-	nC	



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline			Graphic symbol
1	S	Source	F			D
2	S	Source				
3	S	Source				G P
4	G	Gate				mbb076 S
mb	D	Mounting base; connected to drain	LFP	PAK33 (SOT1210)	

6. Ordering information

Table 3. Ordering information

3 · · · · · · · · · · · · · · · · · · ·							
Type number	Package						
	Name	Description	Version				
BUK9M43-100E	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 8 leads	SOT1210				

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9M43-100E	94310E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	100	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω		-	100	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	10	V
		Pulsed; T _j ≤ 175 °C	[1] [2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	75	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	25	Α
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	17.6	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	99	Α
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C

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Symbol	Parameter	Conditions		Min	Max	Unit			
Source-drain	Source-drain diode								
Is	source current	T _{mb} = 25 °C		-	25	Α			
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$		-	99	Α			
Avalanche ruggedness									
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 25 A; $V_{sup} \le 100$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[3] [4]	-	44	mJ			

- [1] Accumulated pulse duration up to 50 hours delivers zero defect ppm.
- 2] Significantly longer life times are achieved by lowering T_i and or V_{GS}
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.

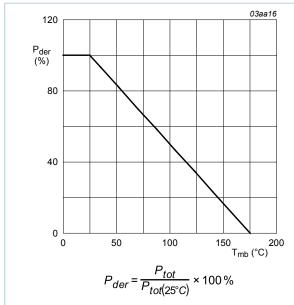


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

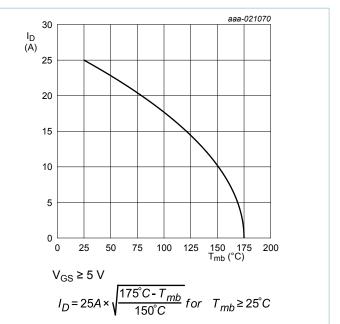
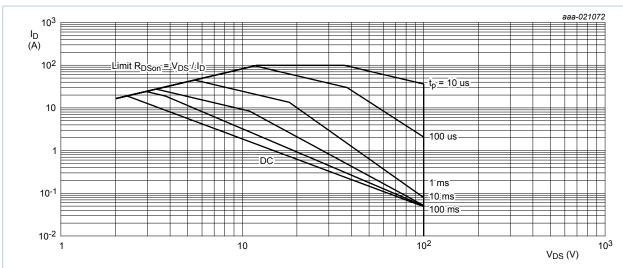


Fig. 2. Continuous drain current as a function of mounting base temperature

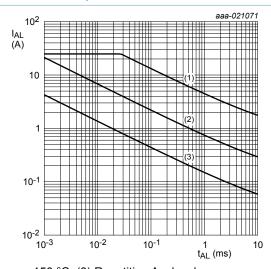
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 T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1) $T_{j \text{ (init)}}$ = 25 °C; (2) $T_{j \text{ (init)}}$ = 150 °C; (3) Repetitive Avalanche

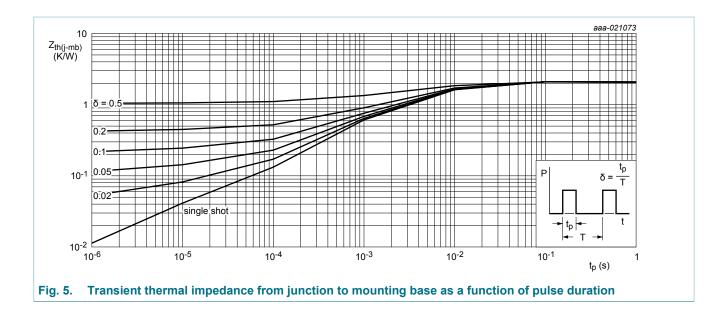
Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	1.82	2	K/W

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					,
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	100	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	90	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	1.4	1.7	2.1	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 10	-	-	2.45	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; Fig. 10	0.5	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.01	1	μΑ
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	35	43	mΩ
		V_{GS} = 10 V; I_D = 5 A; T_j = 25 °C; <u>Fig. 11</u>	-	34	43	mΩ
		V _{GS} = 5 V; I _D = 5 A; T _j = 175 °C; <u>Fig. 12</u>	-	-	121	mΩ
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	$I_D = 5 A; V_{DS} = 80 V; V_{GS} = 5 V;$	-	20.2	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	3.8	-	nC
Q_GD	gate-drain charge		-	8.2	-	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	-	1736	2309	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	111	133	pF

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
C _{rss}	reverse transfer capacitance			-	70	95	pF	
t _{d(on)}	turn-on delay time	V_{DS} = 80 V; R_{L} = 15 Ω ; V_{GS} = 5 V; $R_{G(ext)}$ = 5 Ω ; T_{j} = 25 °C		-	9.8	-	ns	
t _r	rise time			-	16.7	-	ns	
$t_{d(off)}$	turn-off delay time			-	32.1	-	ns	
t _f	fall time			-	17.8	-	ns	
Source-drain diode								
V_{SD}	source-drain voltage	$I_S = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$		-	0.78	1.2	V	
t _{rr}	reverse recovery time	$I_S = 5 \text{ A}; \text{ d}I_S/\text{d}t = -100 \text{ A/}\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $V_{DS} = 25 \text{ V}; \text{ T}_j = 25 \text{ °C}$		-	28.1	-	ns	
Q _r	recovered charge			-	38.1	-	nC	

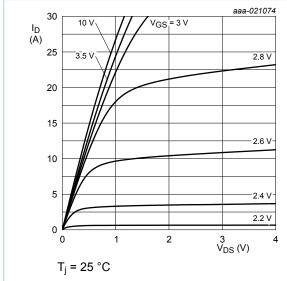


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

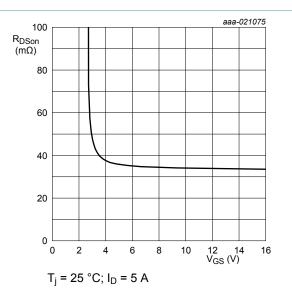


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

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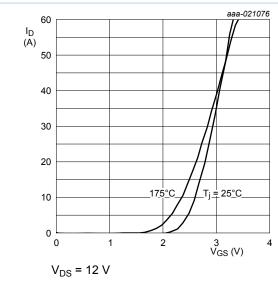


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

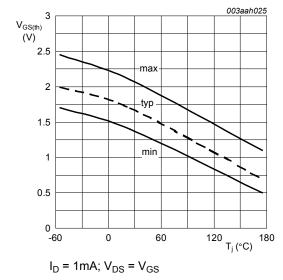


Fig. 10. Gate-source threshold voltage as a function of junction temperature

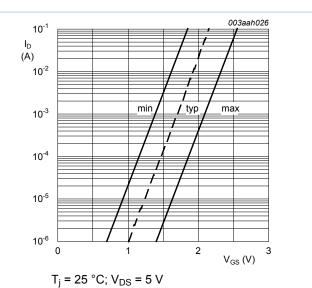


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

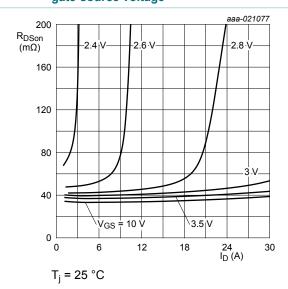


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

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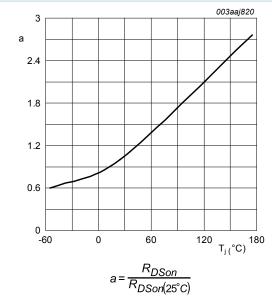


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

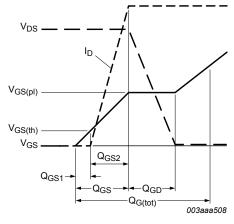


Fig. 14. Gate charge waveform definitions

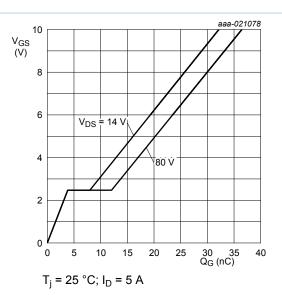


Fig. 13. Gate-source voltage as a function of gate charge; typical values

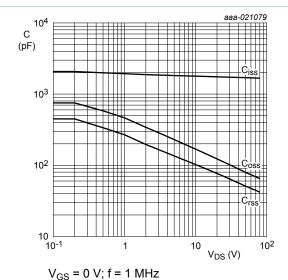
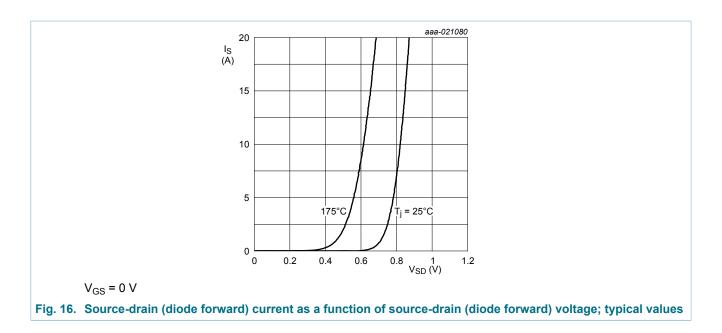


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

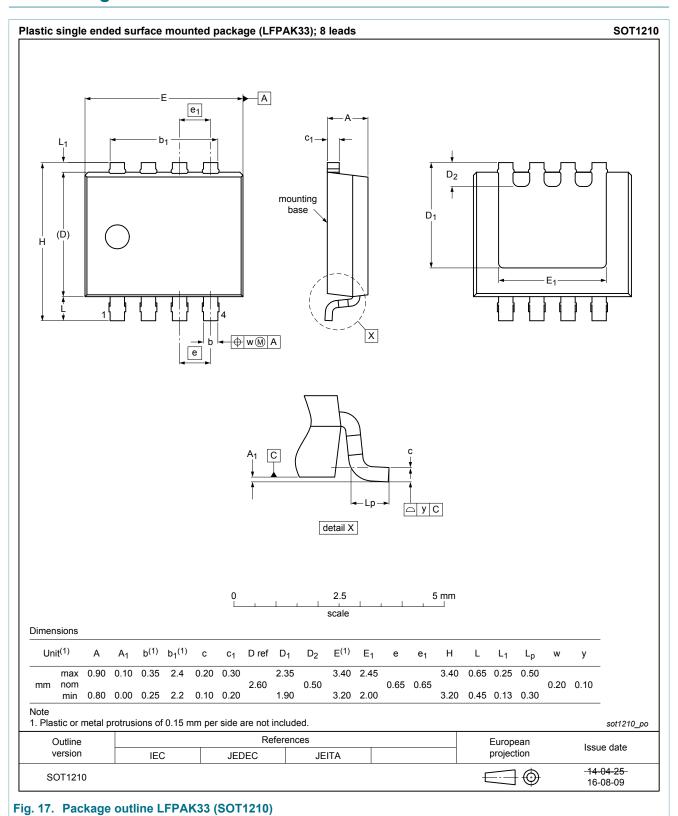
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11. Application information

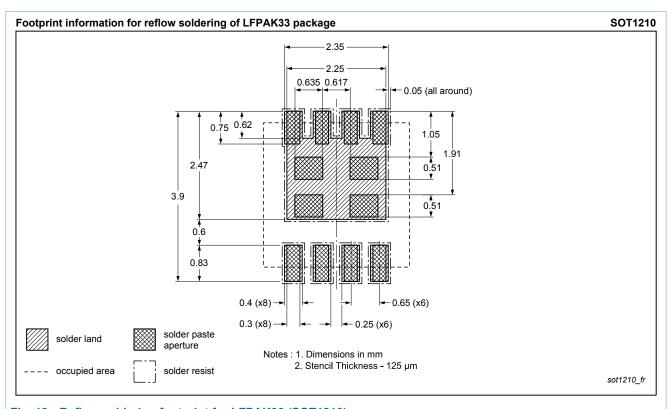
For guidance on how to use and understand this datasheet, please refer to application note <u>AN11158</u> "Understanding power MOSFET datasheet parameters".

12. Package outline



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13. Soldering



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14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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